SEMICONDUCTOR DEVICE WITH REDUCED HIGH VOLTAGE TERMINATION AREA AND HIGH BREAKDOWN VOLTAGE

ABSTRACT

A semiconductor device (12) with reduced high voltage termination area and high breakdown voltage. The device comprises first and second field shield plates (46), (48). The first field shield plate (46) is disposed above a high voltage first impurity region (22) and a junction extension doped region (42) and is in contact with a conductive material (26) which comprises the high voltage terminal of the device (12). A second field shield plate (48) is disposed above a low voltage second impurity region (30) and the junction extension doped region (42) and is covered by an extended portion (35) of a low voltage source contact (34).

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